

Triac

Medium Power Use

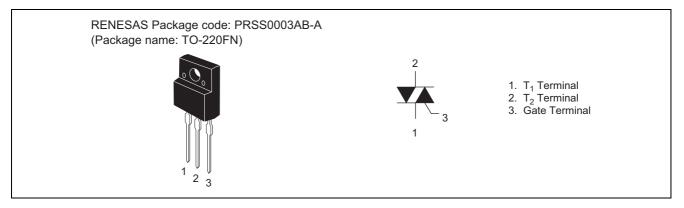
REJ03G0317-0200 Rev.2.00 Mar 06, 2007

Features

- $I_{T(RMS)}: 5 A$
- V_{DRM} : 600 V
- I_{FGTI} , I_{RGTI} , I_{RGTIII} : 20 mA (10 mA)^{Note5}
- Viso : 2000 V
- The product guaranteed maximum junction temperature 150°C.

Outline

- Insulated Type
- Planar Passivation Type
- Refer to the recommended circuit values around the triac before using.



Applications

Switching mode power supply, small motor control, heater control, solenoid driver, and other general purpose control applications

Maximum Ratings

Parameter	Symbol	Voltage class 12	Unit
Repetitive peak off-state voltage ^{Note1}	V _{DRM}	600	V
Non-repetitive peak off-state voltage ^{Note1}	V _{DSM}	720	V

BCR5KM-12LB

Parameter	Symbol	Ratings	Unit	Conditions	
RMS on-state current	I _{T (RMS)}	5	A	Commercial frequency, sine full wave 360° conduction, Tc = 121° C	
Surge on-state current	I _{TSM}	50	A	60Hz sinewave 1 full cycle, peak valu non-repetitive	
I ² t for fusing	l ² t	10.4	A ² s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	
Peak gate power dissipation	P _{GM}	3	W		
Average gate power dissipation	P _{G (AV)}	0.3	W		
Peak gate voltage	V _{GM}	10	V		
Peak gate current	I _{GM}	2	А		
Junction temperature	Tj	- 40 to +150	°C		
Storage temperature	Tstg	- 40 to +150	°C		
Mass	—	2.0	g	Typical value	
Isolation voltage	Viso	2000	V	Ta = 25°C, AC 1 minute, T ₁ ·T ₂ ·G terminal to case	

Notes: 1. Gate open.

Electrical Characteristics

Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state current		I _{DRM}	—	—	2.0	mA	Tj = 150°C, V _{DRM} applied
On-state voltage		V_{TM}	—	—	1.8	V	$Tc = 25^{\circ}C, I_{TM} = 7 A,$
							Instantaneous measurement
Gate trigger voltage ^{Note2}	Ι	V_{FGTI}	—	—	1.5	V	$Tj=25^{\circ}C,\ V_{D}=6\ V,\ R_{L}=6\ \Omega,$
	II	V_{RGTI}	_	—	1.5	V	$R_G = 330 \Omega$
	III	V _{RGTIII}	—	—	1.5	V	
Gate trigger current ^{Note2}	Ι	I _{FGTI}	—	—	20 ^{Note5}	mA	$Tj=25^{\circ}C,\ V_{D}=6\ V,\ R_{L}=6\ \Omega,$
	II	I _{RGTI}	—	—	20 ^{Note5}	mA	R _G = 330 Ω
	III	I _{RGTIII}	—	—	20 ^{Note5}	mA	
Gate non-trigger voltage		V_{GD}	0.2/0.1	—	—	V	$Tj = 125^{\circ}C/150^{\circ}C, V_D = 1/2 V_{DRM}$
Thermal resistance		R _{th (j-c)}	—	—	3.8	°C/W	Junction to case ^{Note3}
Critical-rate of rise of off-state commutating voltage ^{Note4}		(dv/dt)c	5/1	_	—	V/µs	Tj = 125°C/150°C

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

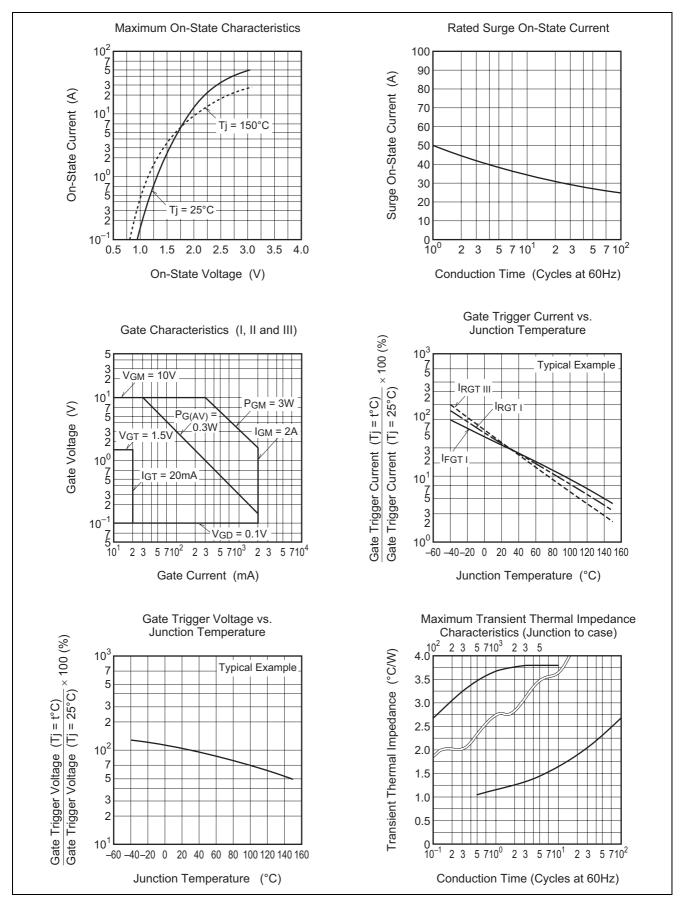
3. The contact thermal resistance $R_{th\,(c\text{-}f)}$ in case of greasing is 0.5°C/W.

4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

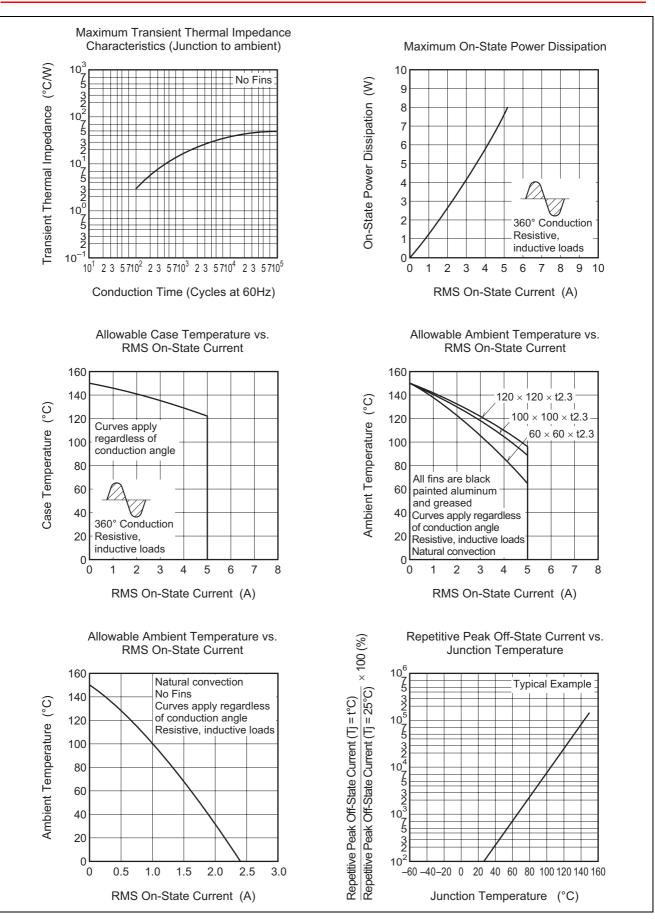
5. High sensitivity ($I_{GT} \le 10$ mA) is also available. (I_{GT} item: 1)

Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature Tj = 125°C/150°C	Supply Voltage Time
2. Rate of decay of on-state commutating current (di/dt)c = - 2.5 A/ms	Main Current → Time
3. Peak off-state voltage V _D = 400 V	Main Voltage Time (dv/dt)c V _D

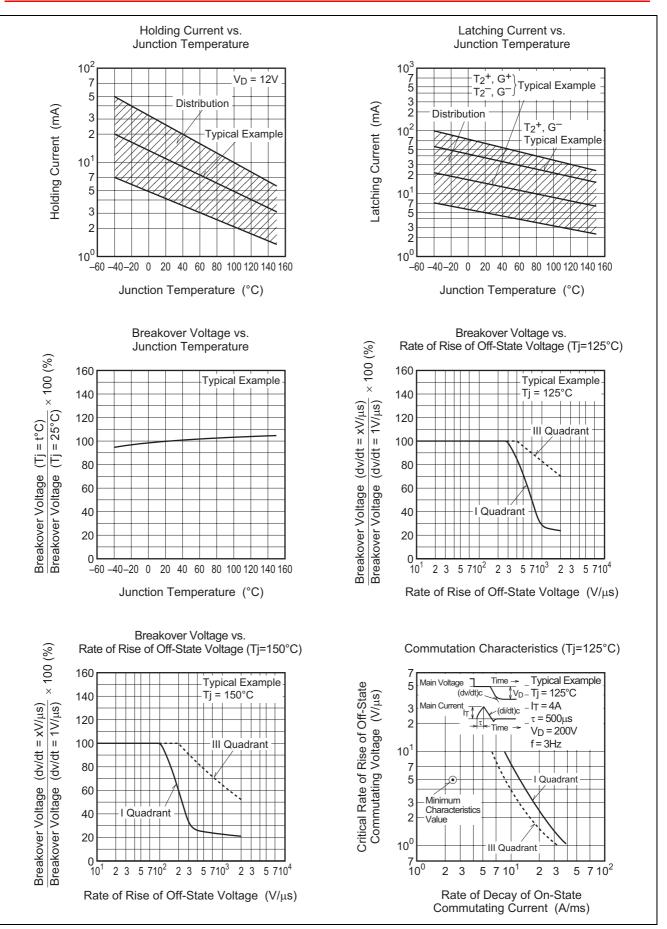
Performance Curves



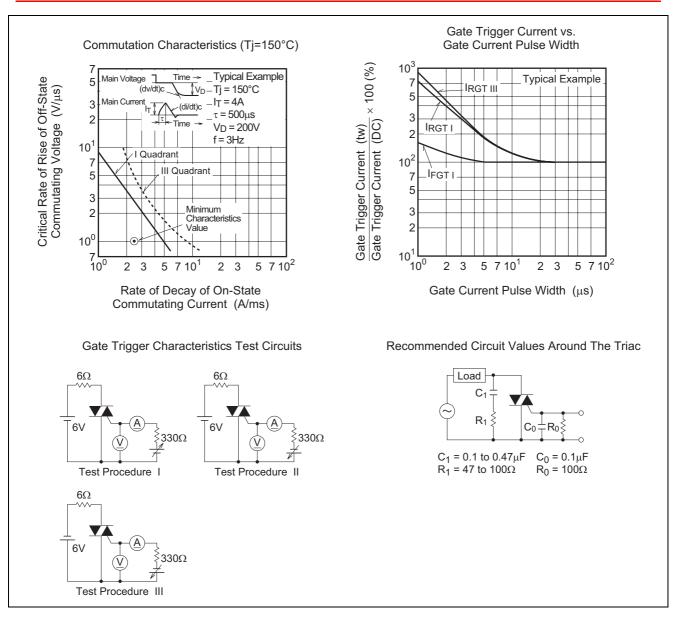




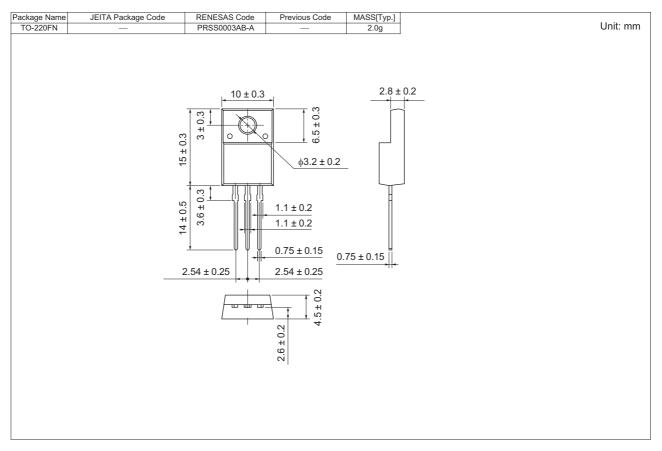




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Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Plastic Magazine (Tube)	50	Type name	BCR5KM-12LB
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR5KM-12LB-A8

Note : Please confirm the specification about the shipping in detail.

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